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最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T _b =25°C)					電気的特性 (T _b =25°C)										外形	備考
				V _{ceo} (V)	V _{ceo} (V)	I _c (mA)	P _c (mW)	T _j (°C)	I _{ceo} 最大値 (μA)	直流又はパルスI _{BE}		バイアス		h _{FE}	h _{FE} h _{FE} * (Ω)	h _{FE} h _{FE} * (×10 ⁻⁴)	h _{FE} h _{FE} * (μS)	f _{αB} f _r * (Mc)		
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
 - 9 f_{αB} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_r.
 - 10 C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
 - 11 OUTLINE
 - 12 REMARKS
- :とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 気 的 特 性 (T _a = 25°C)											外形	備考		
				V _{CEO} (V)	V _{EB0} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CEO} 最大値 (μA)	直流又はパルス hFE		バイアス		h _{FE} h _{FB} *	h _{ie} h _{ib} * (Ω)	h _{re} h _{rb} * (×10 ⁻⁴)	h _{oe} h _{ob} * (μΩ)	f _β f _β * (Mc)	C _{ob} (pF)			f _{β0} h _{β(real)} * (Ω)	
										V _{CE(V)}	I _{C(mA)}	V _{CB(V)}	I _{E(mA)}										
2SC410A	新電元	SW	Si.DB	200	4	10A	100W (T _c =25°C)	150	20mA	200	37	5	5A	10	2A	t _{on} < 1.2 μs, t _{off} < 5 μs t _r < 4 μs			f _β 0.4			102	
" 434A	"	"	"	200	4	30A	100W (T _c =25°C)	150	20mA	200	28	5	10A	10	2A				f _β 0.4			105	
" 487A	東芝	PA	Si.P	150	5	1.5A	15W (T _c =25°C)	150	1mA	30	100	2	200	10	-50				20*	85	5	99	
* " 642A	"	"	Si.TMe	1500	5	1A	50W (T _c =25°C)	150	10	500	30-160	15	150	15	-200				2*	55	10	102	水平偏向用
* " 643A	"	"	"	1500	5	2.5A	50W (T _c =25°C)	150	10	500	> 5	15	2A	15	-100	t _f < 1 μs			3*	95	10	102	水平偏向用
* " 680A	日立	"	Si.T	200	6	2A	12.5W (T _c =25°C)	150	1	30	180	10	200									153	
* " 681A	"	"	"	250	5	6A	50W (T _c =25°C)	150	I _{CBX} 15mA	30						t _f < 0.5 μs						102	水平偏向用
* " 685A	"	"	Si.TPa	300	4	100	6.5W (T _c =70°C)	150			60	10	50									153	
" 711A	三菱	RF.AF	Si.EP	50	4	100	200	125	0.1	25	250	6	1	6	-1	8500			150*	2.5	C _e f _{β0} 200 pS	138B	
" 782A	東芝	PA	Si.TP	300	5	1.5A	25W (T _c =25°C)	150	30	300	150	10	100	10	-100				10*	70	25	99	
" 914A	富士通 半導体 日立	SW	Si.EP	40	5	300	300	175	0.2	20	70	1	30	h _{FE} > 14 (2V, 300mA)		t _{on} < 80ns, t _{off} < 86ns t _{stg} < 65ns						49C	
" 915A	"	"	"	30	5	300	300	175	0.2	20	70	1	30	h _{FE} > 15 (2V, 200mA)		t _{on} < 45ns, t _{off} < 42ns t _{stg} < 27ns						49C	
" 926A	ソニー	RF.AF.SW	Si.DB	210	5	30	320	120	0.2	150	100	3	1	10	-10	4500			160*	2.2	C _e f _{β0} 40 pS	38	
" 936A	日立	PA	Si.TMe	1000	5	1A	22W (T _c =25°C)	150	10	500	45	10	100	15	-200				7*	35	25	102	
" 985A	日電	RF.LN	Si.E	20	3	40	300	200	0.1	10	100	10	15	10	-15	NF=4dB (10V, -3mA, 2GHz)			3700*	0.6	20*	26	
" 987A	"	"	"	20	3	30	250	200	0.1	10	100	10	10	10	-10	NF=3dB (10V, -3mA, 2GHz)			4500*	C _{rr} 0.4	20*	26	
" 988A	"	RF	"	20	3	30	200	200	0.1	10	100	10	10	10	-10	NF < 2dB (10V, -3mA, 500MHz)			3000*	C _{rr} 0.5	30*	50C	
" 988B	"	"	"	20	3	30	200	200	0.1	10	100	10	10	10	-10	NF < 1.5dB (10V, -3mA, 500MHz)			3000*	C _{rr} 0.5	30*	50C	
* " 999A	東芝	RF.PA.SW	Si.TMe	1500	5	2.5A	50W (T _c =25°C)	150	10	500	30	15	200	15	-200				4	80	10	102	
* " 1005A	"	PA	"	1400	5	5A	50W (T _c =25°C)	150	10	500	12	15	4A	15	-500				3*	150	5	102	
" 1012A	松下	RF.AF	Si.TP	250	5	60	2.5W (T _c =25°C)	175	2	12	60	20	40	10	-3	35			100*	3.5	C _e f _{β0} 60 pS	84B	
* " 1122A	東芝	PA	Si.EP	35	4	4.5A	30W (T _c =25°C)	175	50	15	40	5	1.5A	10	-200				400*	20	5*	135	
* " 1151A	三菱	RF.PA	Si.EMe	1000	5	1A	50W (T _c =25°C)	125	200	500	60	10	150	15	-200				5*	65	25	102	
* " 1153A	"	SW	"	1400	6	2.5A	50W (T _c =25°C)	125	1mA	1400	20	10	2.5A			t _r < 1.5 μs, t _f < 3 μs t _{stg} < 2 μs						102	
* " 1172A	東芝	PA	Si.TMe	1500	5	5A	50W (T _c =25°C)	150	10	500	20	10	2A	10	-500	t _f < 1 μs			2*	165	10	102	水平偏向用
" 1212A	日立	PA	Si.EPa	80	4	1A	8W (T _c =25°C)	150	5	50	60-200	4	50	4	-30				160*	30		160	2SA743A (コンパリ)
" 1213A	"	AF	"	50	4	500	400	125	0.5	20	60-320	3	10								138	2SA673A とコンパリ	
" 1226A	松下	PA	"	50	5	2A	10W (T _c =25°C)	150	1	20	120	5	1A	5	-500				150*	50	3.3*	161	2SA699A とコンパリ
" 1280A	日電	RF	Si.E テリント	40	10	300	250	125	0.1	20	30,000	2	100	10	-10				180*	5	220*	138	
* " 1367A	日立	PA	Si.TMe	1000	5	1A	50W (T _c =25°C)	125	10	500	45	10	200	15	-200				6*	60	25	102	